

DF252

FAST RECOVERY DIODE

APPLICATIONS

- Induction Heating.
- A.C. Motor Drives.
- Inverters And Choppers.
- Welding.
- High Frequency Rectification.
- UPS.

KEY PARAMETERS

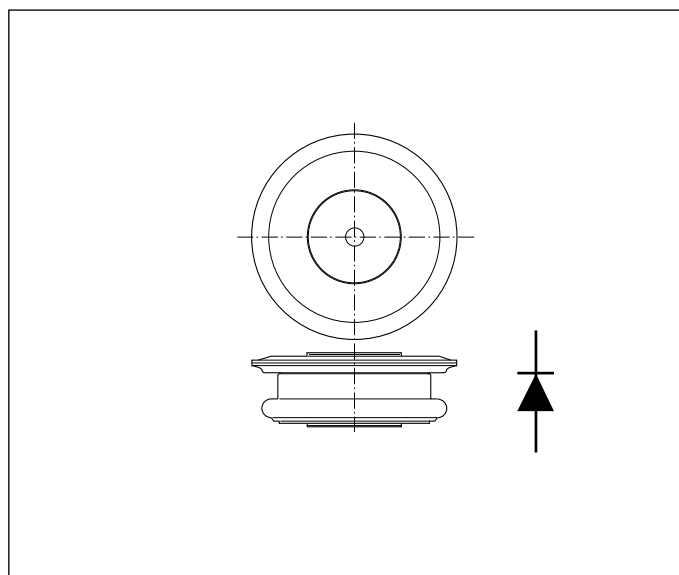
V_{RRM}	1600V
$I_{F(AV)}$	360A
I_{FSM}	3000A
Q_r	35 μ C
t_{rr}	3.2 μ s

FEATURES

- Double Side Cooling.
- High Surge Capability.
- Low Recovery Charge.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DF252 16 DF252 14 DF252 12 DF252 10 DF252 08 DF252 06	1600 1400 1200 1000 800 600	$V_{RSM} = V_{RRM} + 100V$



Outline type code: M771. Turn to page 8 for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	360	A
$I_{F(RMS)}$	RMS value	$T_{case} = 65^{\circ}C$	560	A
I_F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	500	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	276	A
$I_{F(RMS)}$	RMS value	$T_{case} = 65^{\circ}C$	435	A
I_F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	375	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% V_{RRM} , $T_j = 150^\circ\text{C}$	3.0	kA
I^2t	I^2t for fusing		45×10^3	A^2s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% V_{RRM} , $T_j = 150^\circ\text{C}$	2.4	kA
I^2t	I^2t for fusing		28.8×10^3	A^2s

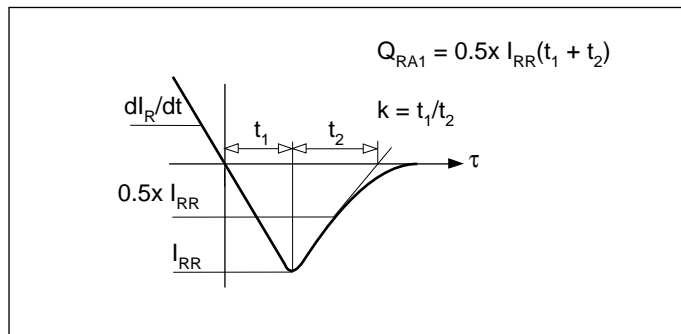
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.07	$^\circ\text{C/W}$
		Single side cooled	Anode dc	-	0.133	$^\circ\text{C/W}$
			Cathode dc	-	0.147	$^\circ\text{C/W}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 3.5kN with mounting compound	Double side	-	0.02	$^\circ\text{C/W}$
			Single side	-	0.04	$^\circ\text{C/W}$
T_{vj}	Virtual junction temperature	On-state (conducting)		-	150	$^\circ\text{C}$
T_{stg}	Storage temperature range			-55	150	$^\circ\text{C}$
-	Clamping force			3.0	4.0	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 450A peak, $T_{case} = 25^{\circ}C$	-	1.6	V
I_{RRM}	Peak reverse current	At V_{RRM} , $T_{case} = 125^{\circ}C$	-	20	mA
t_{rr}	Reverse recovery time	$I_F = 750A$, $di_{RR}/dt = 100A/\mu s$ $T_{case} = 125^{\circ}C$, $V_R = 100V$	3.2	-	μs
Q_{RA1}	Recovered charge (50% chord)		-	35	μC
I_{RM}	Reverse recovery current		-	21	A
K	Soft factor		1.5	-	-
V_{TO}	Threshold voltage	At $T_{vj} = 150^{\circ}C$	-	1.0	V
r_T	Slope resistance	At $T_{vj} = 150^{\circ}C$	-	1.33	$m\Omega$
V_{FRM}	Forward recovery voltage	$di/dt = 1000A/\mu s$, $T_j = 125^{\circ}C$	-	50	V

DEFINITION OF K FACTOR AND Q_{RA1}



CURVES

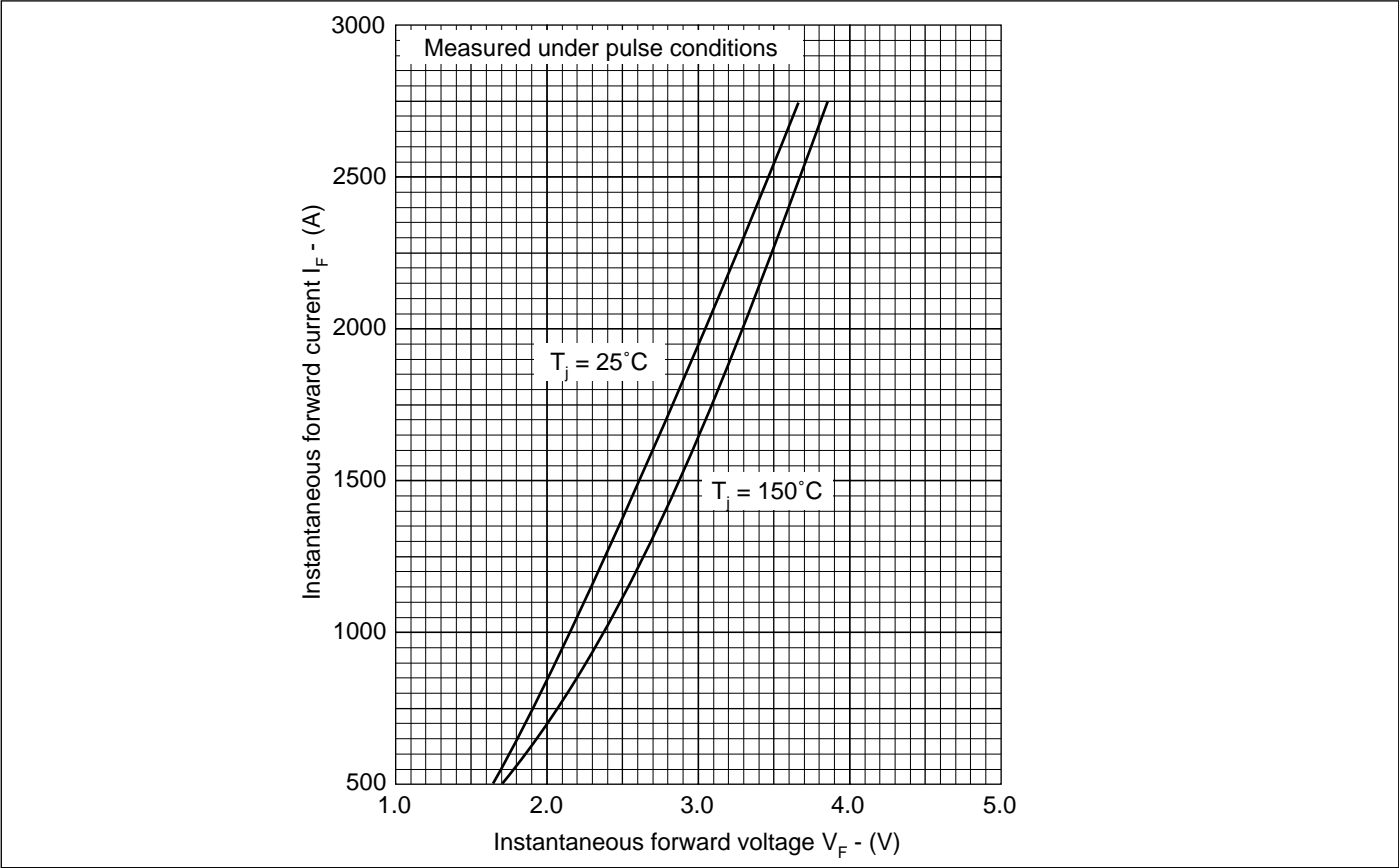


Fig.1 Maximum (limit) forward characteristics

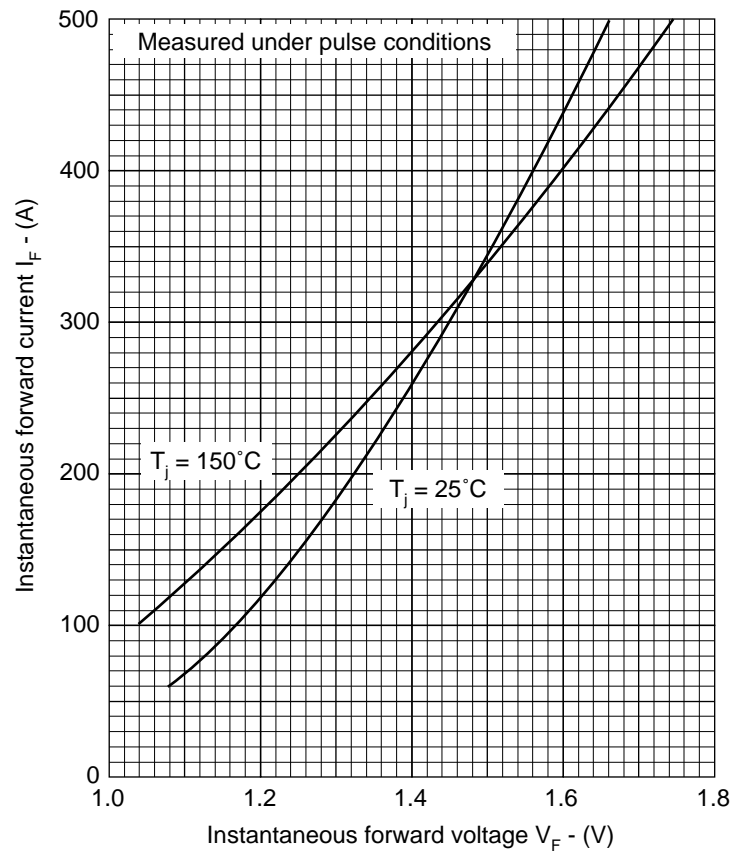


Fig.2 Maximum (limit) forward characteristics

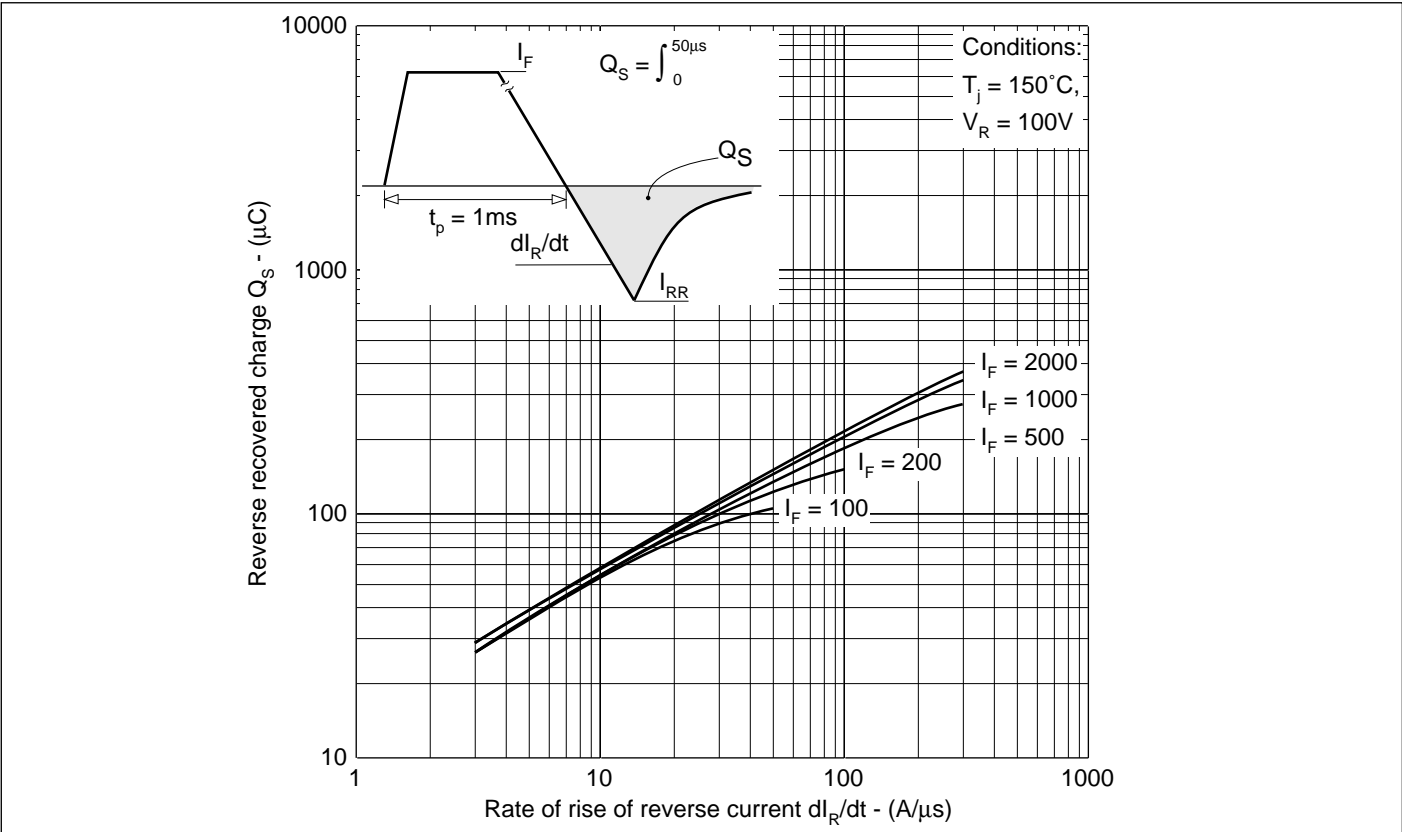


Fig.3 Recovered charge

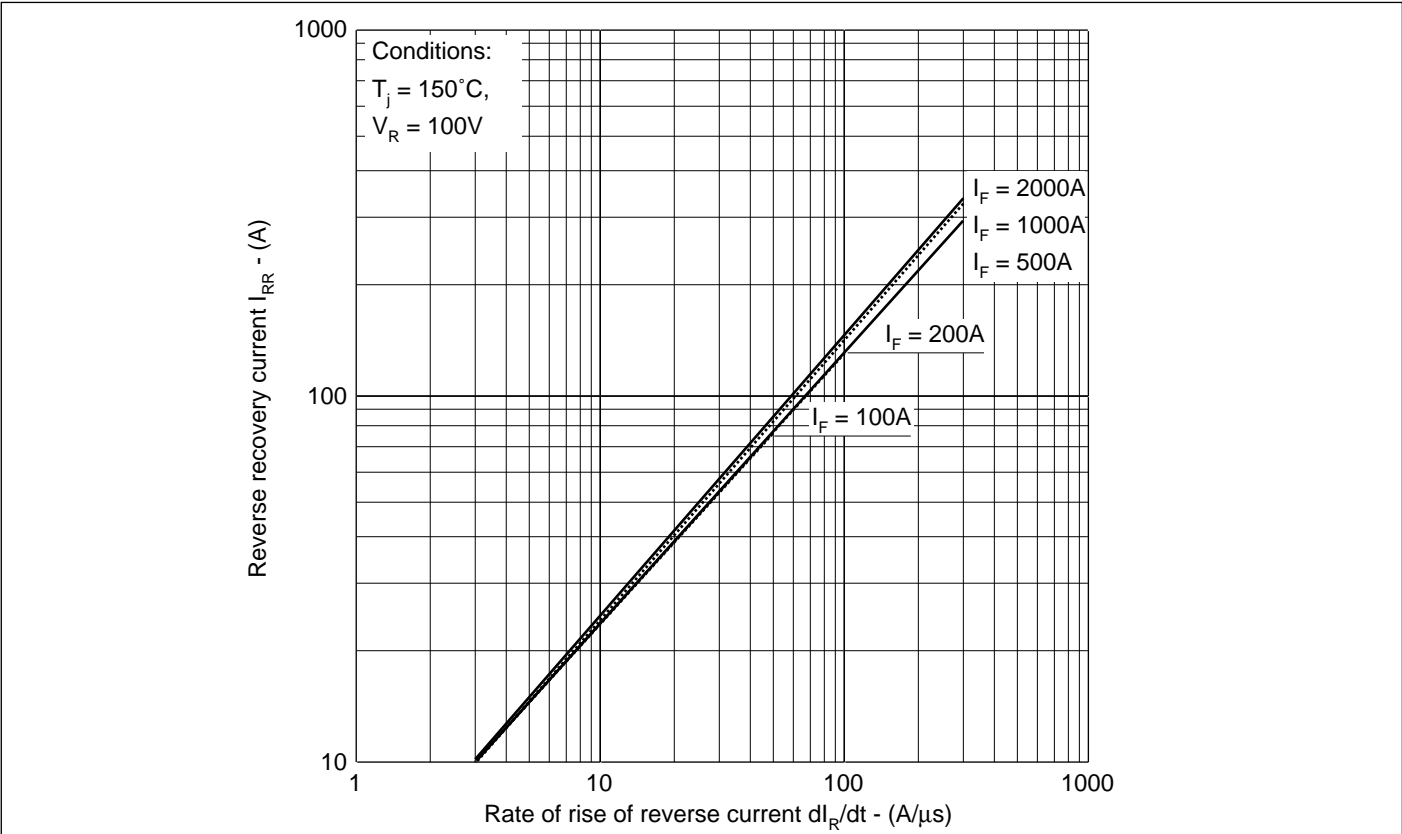


Fig.4 Typical reverse recovery current vs rate of fall of forward current

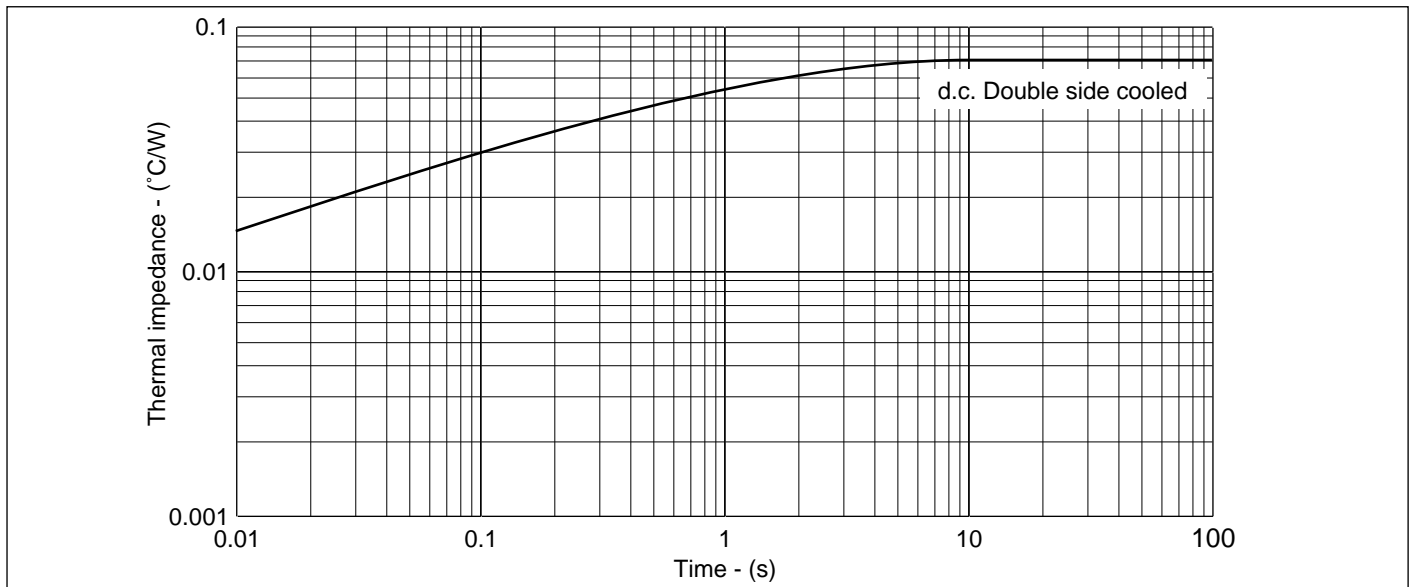
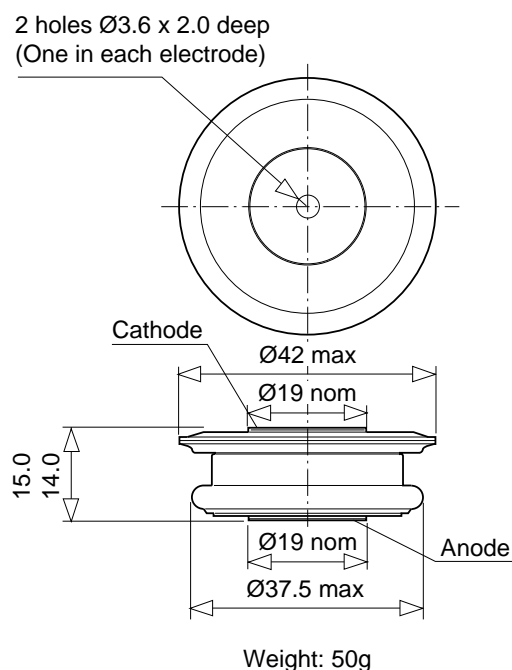


Fig.5 Maximum (limit) transient thermal impedance - junction to case - (°C/W)

PACKAGE DETAILS - M771

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



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